

MMBT6428

NPN General Purpose Amplifier

- This device designed for general pupose amplifier applications at collector currents to 300mA
- Sourced from process 10.



1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings* T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	50	V
V _{CBO}	Collector-Base Voltage	60	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Off Characteristics						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 1.0 \text{mA}, I_B = 0$	50		V	
V _{(BR)CBO}	Collector-Base BreakdownVoltage	$I_C = 100\mu A, I_E = 0$	60		V	
I _{CEO}	Collector Cut-off Current	$V_{CE} = 30V, I_{B} = 0$		0.1	μΑ	
I _{CBO}	Collector Cut-off Current	$V_{CB} = 30V, I_{E} = 0$		10	nA	
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5.0V, I_B = 0$		10	nA	
On Charact	eristics		•		•	
h _{FE}	DC Current Gain	$\begin{aligned} &V_{CE} = 5.0 \text{V, I}_{C} = 10 \mu\text{A} \\ &V_{CE} = 5.0 \text{V, I}_{C} = 100 \mu\text{A} \\ &V_{CE} = 5.0 \text{V, I}_{C} = 1.0 \text{mA} \\ &V_{CE} = 5.0 \text{V, I}_{C} = 10 \text{mA} \end{aligned}$	250 250 250 250	650		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA		0.2 0.6	V	
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 5.0V, I_{C} = 1.0mA$	0.56	0.66	V	
Small Signa	I Characteristics		•		•	
f _T	Current gain Bandwidth Product	$V_{CE} = 5.0V, I_{C} = 1.0mA,$ f = 100MHz	100	700	MHz	
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$		3.0	pF	
C _{ibo}	Input Capacitance	$V_{EB} = 0.5V, I_{C} = 0, f = 1.0MHz$		8.0	pF	

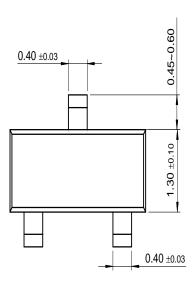
^{*}Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

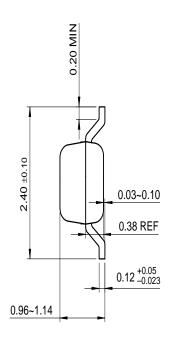
Thermal Characteristics T _A =25°C unless otherwise noted					
Symbol	Parameter	Max.	Units		
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C		
$R_{\theta JC}$	Thermal Resistance, Junction to Case		°C/W		
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W		

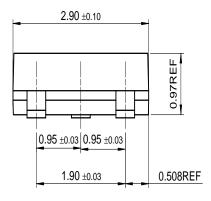
^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

Package Dimensions

SOT-23







Dimensions in Millimeters

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